

Figure 1. Schematic of TiN_x EE-ALD process with reactive background gas (RBG) showing alternating TDMAT precursor doses and low energy electron exposures separated by pumping. NH_3 RBG is present in the reactor during the EE-ALD cycles.

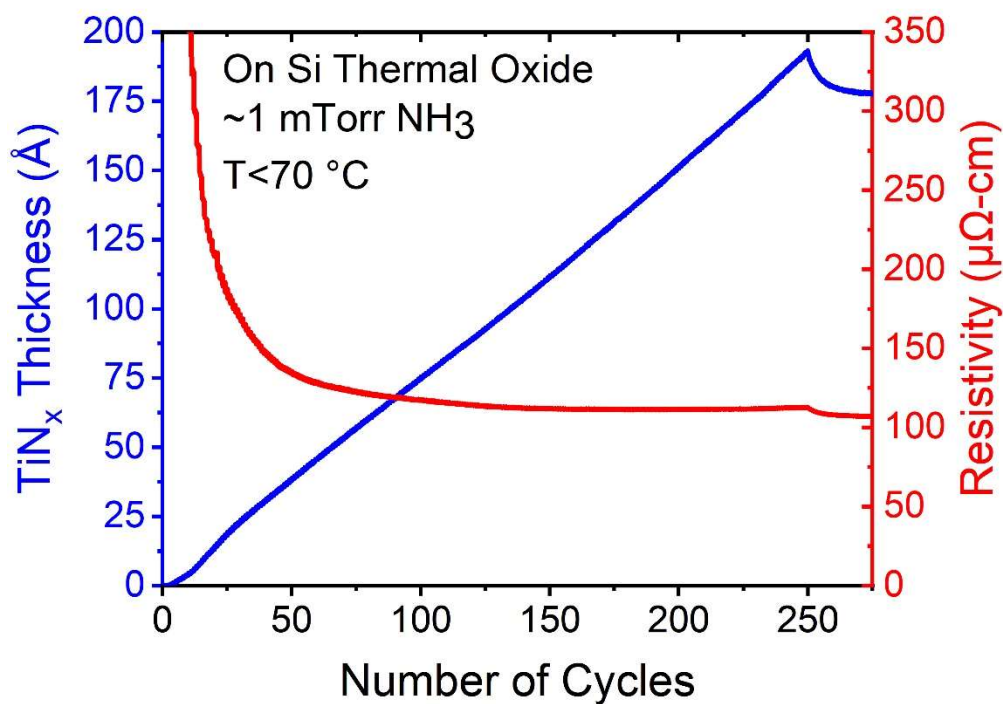


Figure 2. In situ ellipsometry of TiN_x thickness and resistivity on thermal SiO_2 versus number of EE-ALD cycles. The NH_3 RBG was at a pressure of ~ 1 mTorr.